

General Features

- Low On-Resistance
- 100% avalanche tested
- Fast Switching Speed
- Excellent package for good heat dissipation

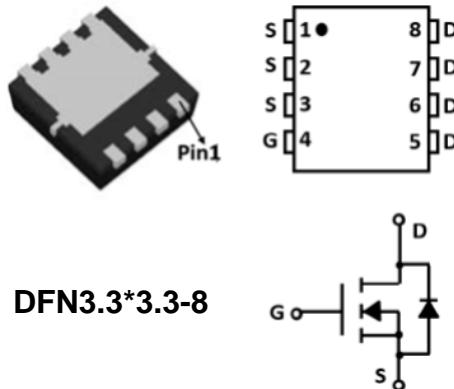
Application

- DC/DC Converters
- On board power for server
- Synchronous rectification

Product Summary



V_{DS}	40	V
$R_{DS(on),Typ} @ V_{GS}=10\text{ V}$	6.0	$\text{m}\Omega$
I_D	40	A



Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	40	A
		$T_C = 100^\circ\text{C}$	32	A
I_{DM}	Pulsed Drain Current ^{note1}		160	A
EAS	Single Pulsed Avalanche Energy		50	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	65	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.92	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$



ASCENDSEMI

ASDM40N40E

40V N-Channel MOSFET

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	LIMITS			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{DS}}=250\mu\text{A}$	40	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$	---	---	1	μA
		$T_J=125^\circ\text{C}$	---	---	30	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{DS}}=250\mu\text{A}$	1.1	1.6	2.4	V
I_{GSS}	Gate Leakage Current	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
$R_{\text{DS}(\text{ON})}^{(1)}$	Drain-Source On-state Resistance	$V_{\text{GS}}=4.5\text{V}, I_{\text{DS}}=20\text{A}$	---	7.5	12	$\text{m}\Omega$
		$V_{\text{GS}}=10\text{V}, I_{\text{DS}}=30\text{A}$	---	6.0	8.5	$\text{m}\Omega$
Diode Characteristics						
$V_{\text{SD}}^{(1)}$	Diode Forward Voltage	$I_{\text{SD}}=20\text{A}, V_{\text{GS}}=0\text{V}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_{\text{SD}}=20\text{A}, dI_{\text{SD}}/dt=100\text{A}/\mu\text{s}$	---	14	---	ns
Q_{rr}	Reverse Recovery Charge		---	32	---	nC
Dynamic Characteristics ⁽²⁾						
R_{G}	Gate Resistance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=0\text{V}, F=1\text{MHz}$	---	1.2	---	Ω
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=20\text{V}, \text{Frequency}=1.0\text{MHz}$	---	1733	---	pF
C_{oss}	Output Capacitance		---	283	---	
C_{rss}	Reverse Transfer Capacitance		---	141	---	
$t_{\text{d}(\text{ON})}$	Turn-on Delay Time	$V_{\text{DD}}=20\text{V}, I_{\text{DS}}=20\text{A}, V_{\text{GEN}}=10\text{V}, R_{\text{G}}=4.7\Omega$	---	6	---	ns
t_{r}	Turn-on Rise Time		---	10	---	
$t_{\text{d}(\text{OFF})}$	Turn-off Delay Time		---	24	---	
t_{f}	Turn-off Fall Time		---	5	---	
Gate Charge Characteristics ⁽²⁾						
Q_{g}	Total Gate Charge	$V_{\text{DS}}=32\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{DS}}=20\text{A}$	---	18	23	nC
Q_{gs}	Gate-Source Charge		---	2.5	---	
Q_{gd}	Gate-Drain Charge		---	5	---	

Notes:

⁽¹⁾Pulse test; Pulse width $\leqslant 300\mu\text{s}$, duty cycle $\leqslant 2\%$.

⁽²⁾Guaranteed by design, not subject to production testing.

Test Circuit

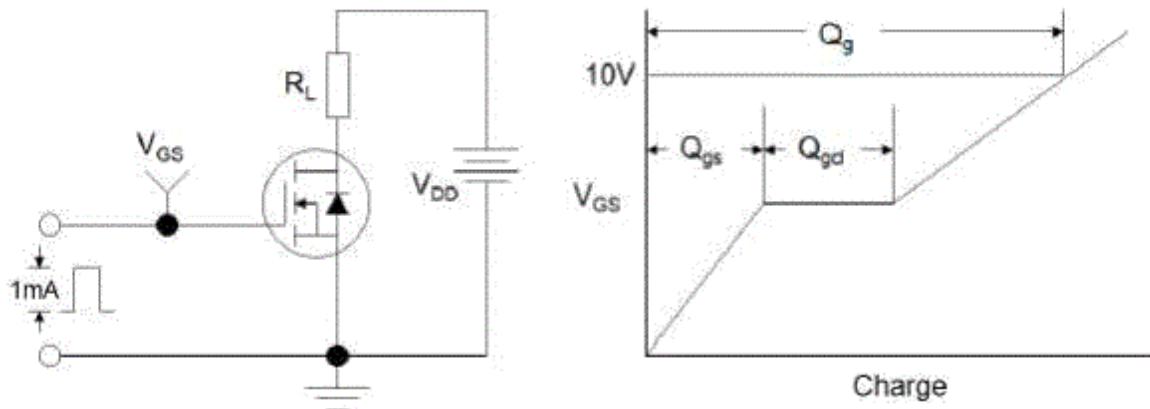


Figure 1: Gate Charge Test Circuit & Waveform

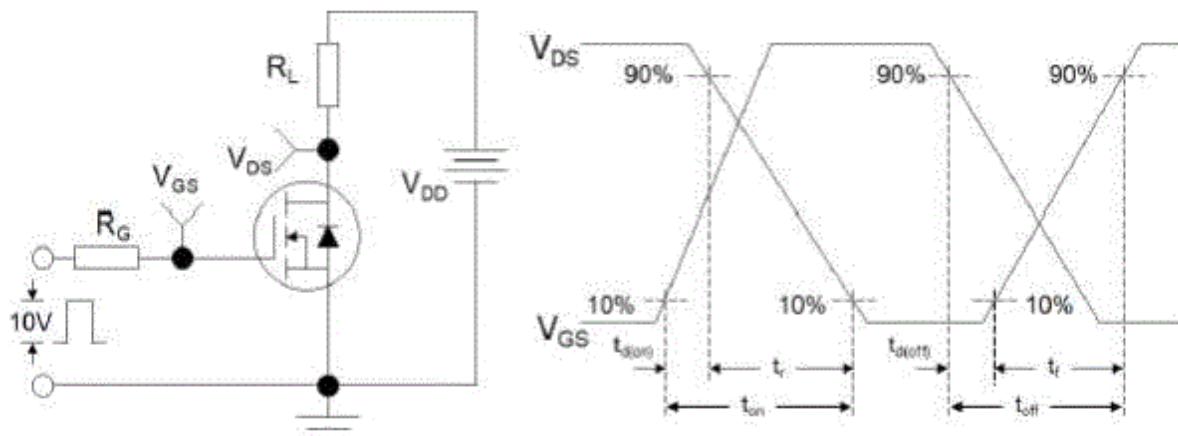


Figure 2: Resistive Switching Test Circuit & Waveforms

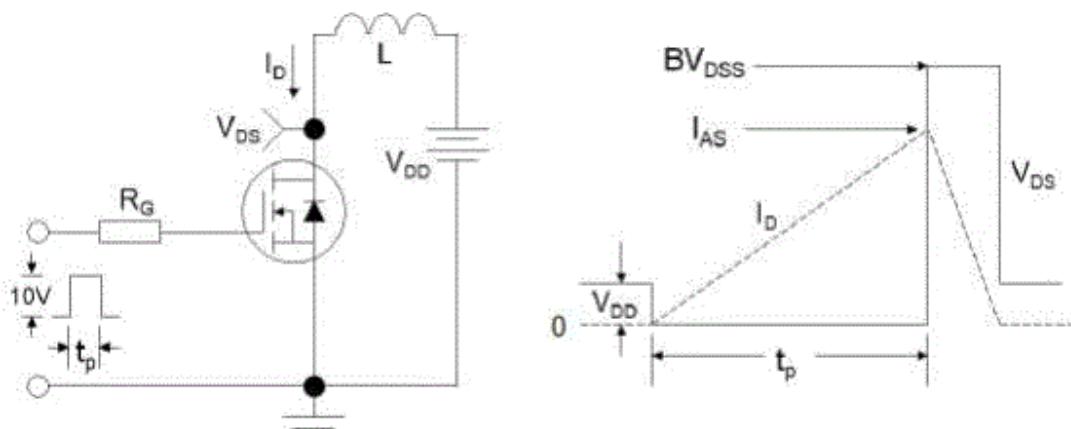
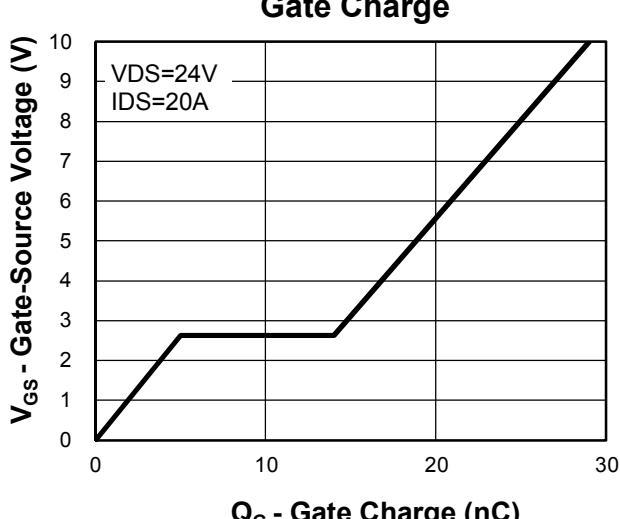
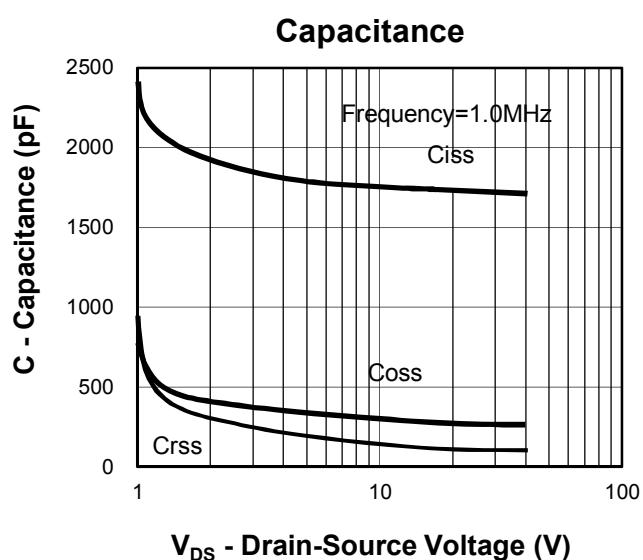
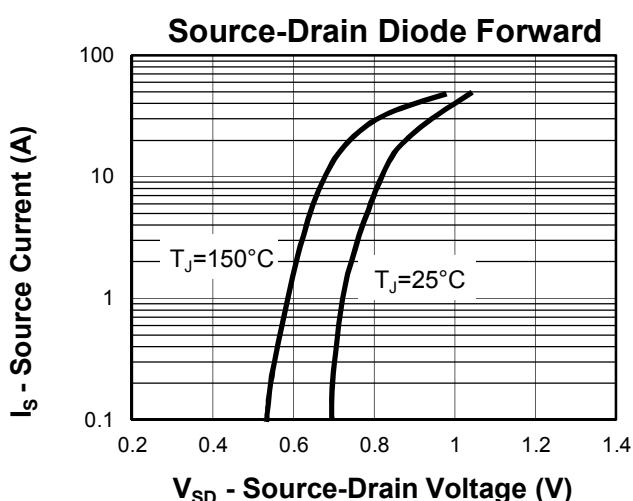
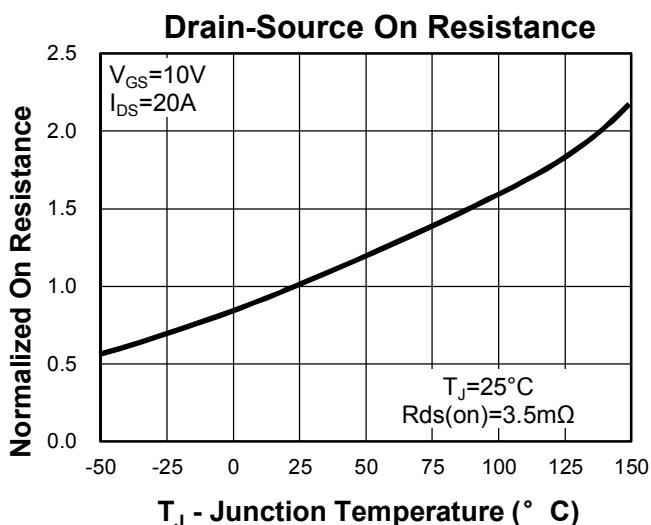
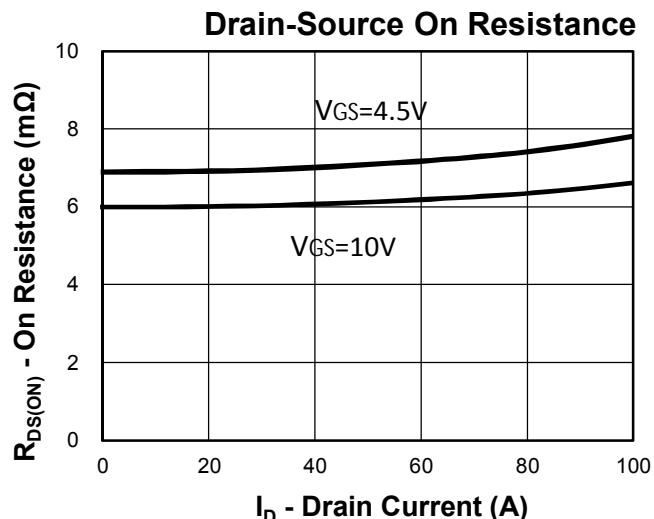
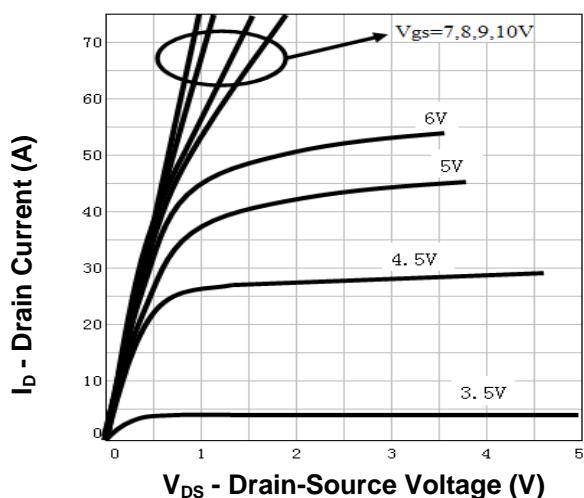
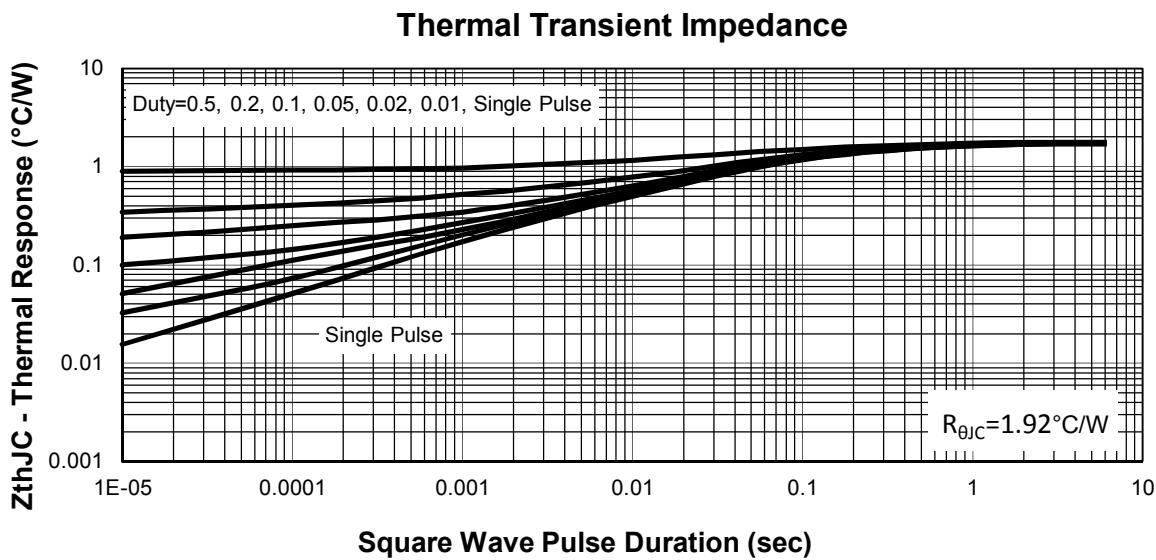
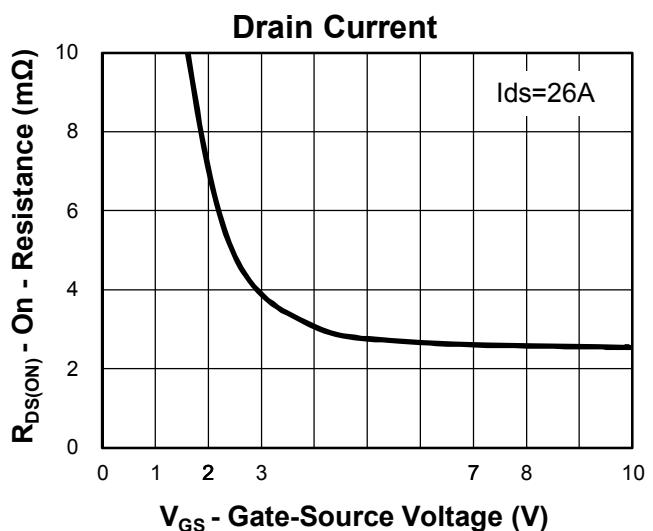
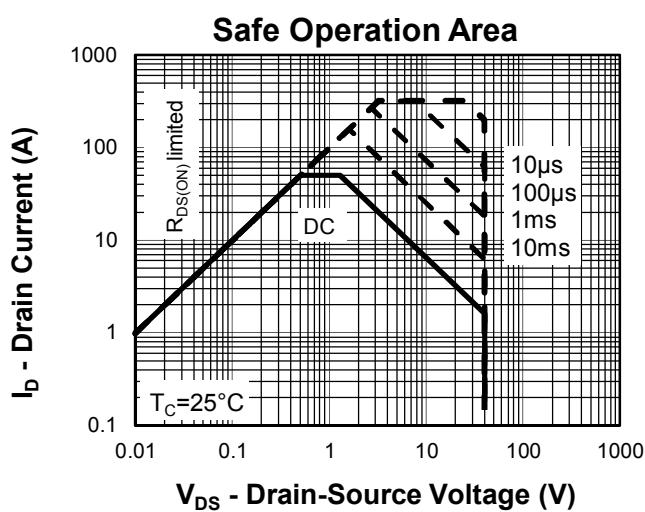
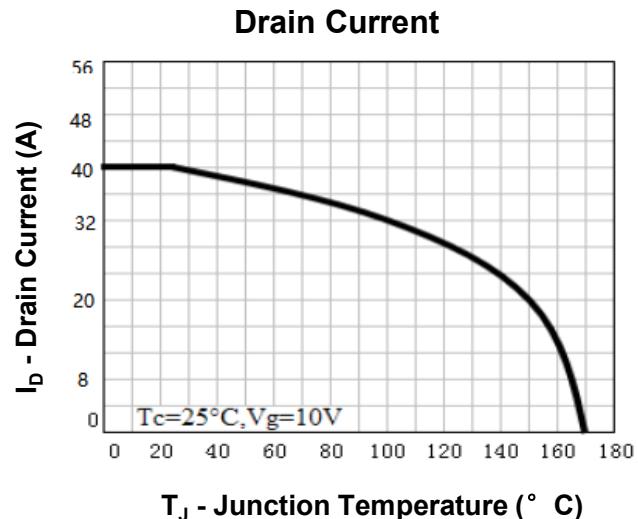
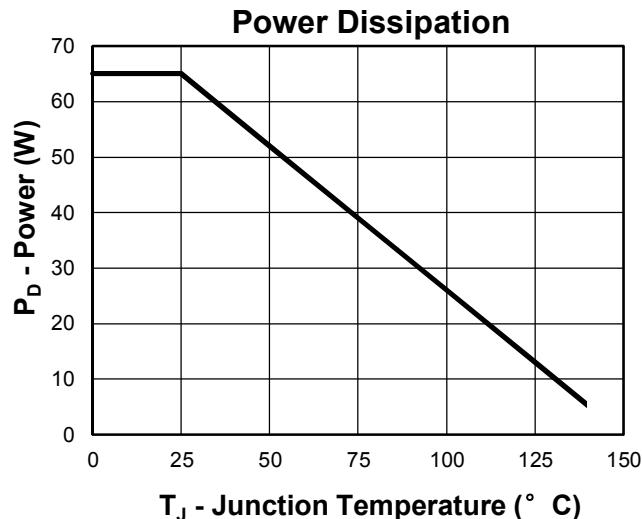


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

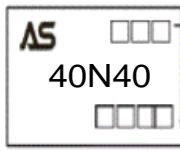
Typical Electrical and Thermal Characteristics (Curves)



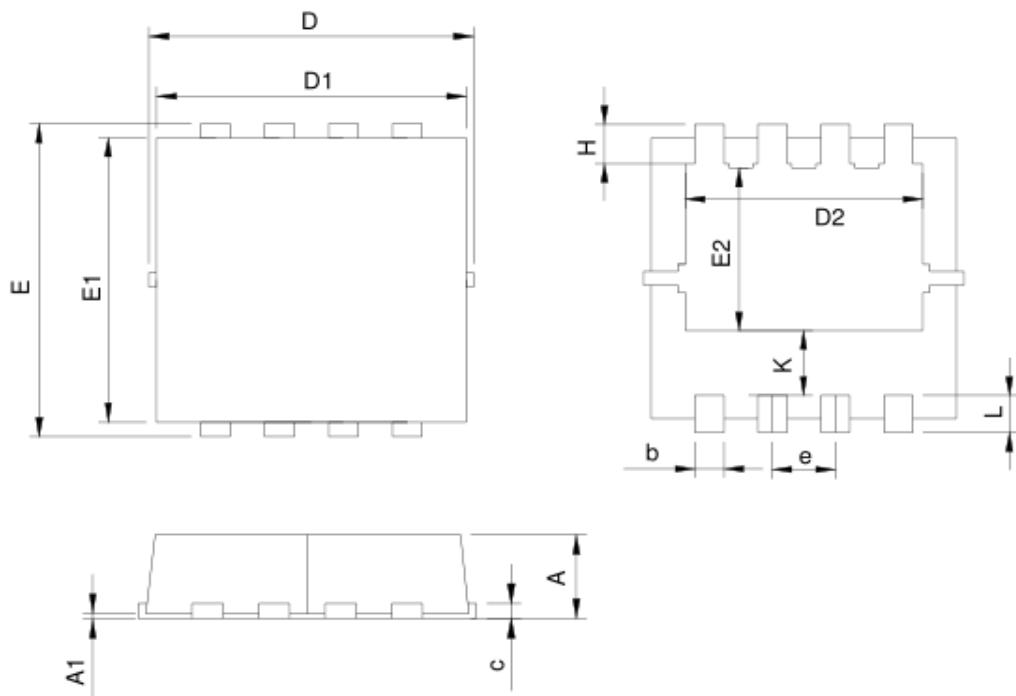


Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM40N40E-R	40N40	DFN3.3*3.3-8	Tape&Reel	5000/Reel

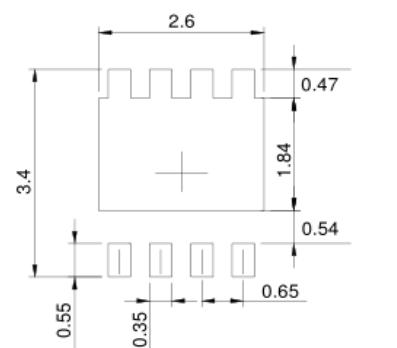
PACKAGE	MARKING
DFN3.3x3.3-8	 AS □□□ → Lot Number 40N40 □□□□ → Date Code

Dimensions(DFN3.3x3.3-8)



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm

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[405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T\)](#) [751625C](#) [PSMN4R2-30MLD](#)
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